

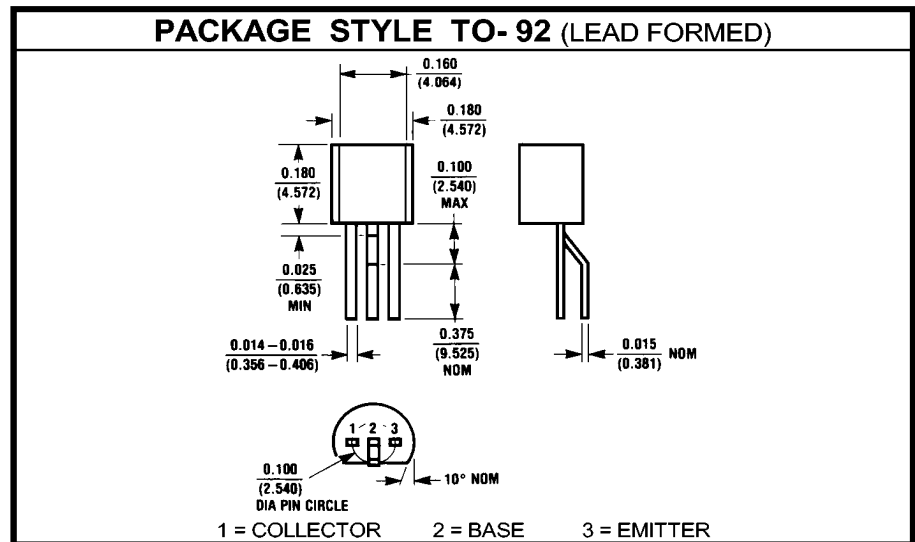
SILICON PNP TRANSISTOR

DESCRIPTION:

The **2N3645-92** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	-60 V
P_{DISS}	700 mW @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+125^\circ\text{C}$
T_{STG}	-55°C to $+125^\circ\text{C}$
θ_{JC}	143 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$			-60V			
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$			-60V			
I_{CES}	$V_{CE} = -50\text{ V}$ $V_{CE} = -50\text{ V}$	$V_{BE} = 0\text{ V}$ $V_{CE} = -50\text{ V}$	$T_C = 65^\circ\text{C}$			35 2.0	nA μA
BV_{EBO}	$I_E = 10\text{ }\mu\text{A}$			-5.0V			
h_{FE}	$V_{CE} = -10\text{ V}$ $V_{CE} = -2.0\text{ V}$	$I_C = 100\text{ }\mu$ $I_C = 1.0\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 50\text{ mA}$ $I_C = 150\text{ mA}$ $I_C = 300\text{ mA}$		40 80 100 115 100 20		300 300	---
$V_{CE(SAT)}$	$I_C = 150\text{ mA}$ $I_C = 300\text{ mA}$	$I_B = 15\text{ mA}$ $I_B = 30\text{ mA}$				-0.4 -1.0	V
$V_{BE(SAT)}$	$I_C = 150\text{ mA}$ $I_C = 300\text{ mA}$	$I_B = 15\text{ mA}$ $I_B = 30\text{ mA}$				-1.3 -2.0	V
f_t	$V_{CE} = -20\text{ V}$	$I_C = 20\text{ mA}$	$f = 100\text{ MHz}$	2.0			
C_{ob}	$V_{CB} = -10\text{ V}$		$f = 1.0\text{ MHz}$			8.0	pF
C_{ib}	$V_{EB} = -0.5\text{ V}$		$f = 1.0\text{ MHz}$			25	pF
t_{on}	$I_C \cong 300\text{ mA}$	$I_{B1} \cong 30\text{ mA}$				40	nS
t_{off}	$I_C \cong 300\text{ mA}$	$I_{B1} = I_{B2} \cong 30\text{ mA}$				100	nS

ADVANCED SEMICONDUCTOR, INC.

REV. A

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